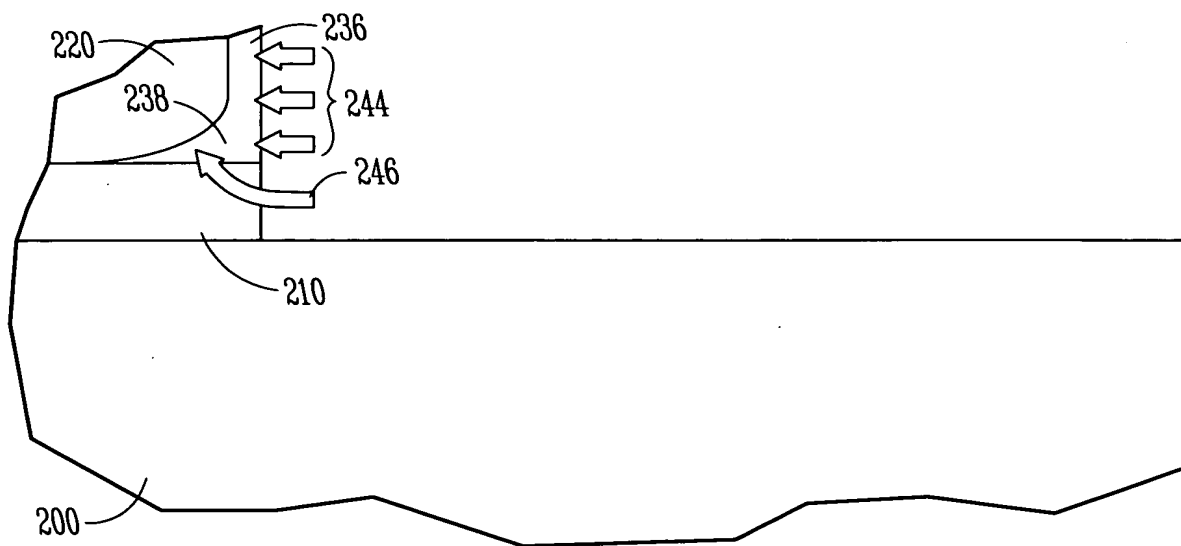
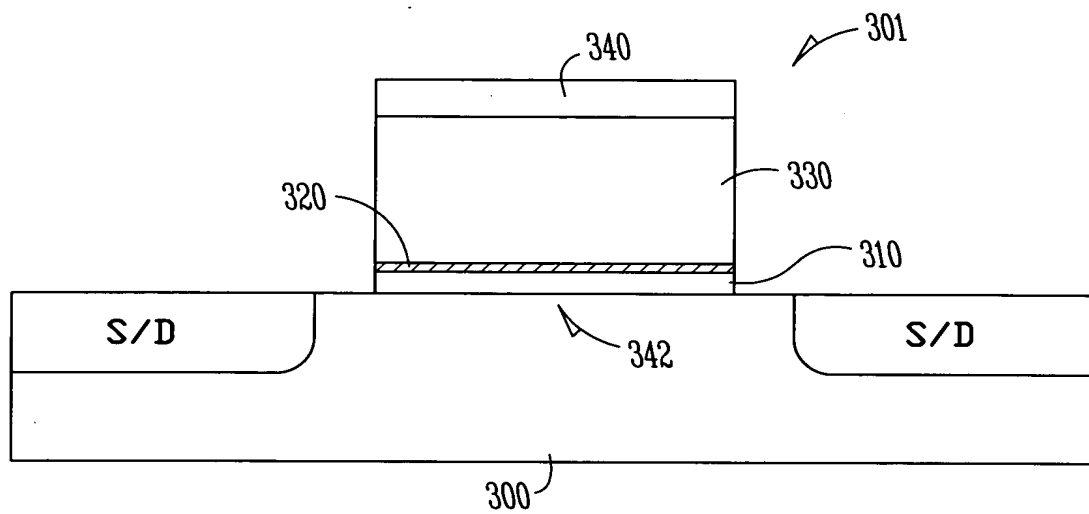


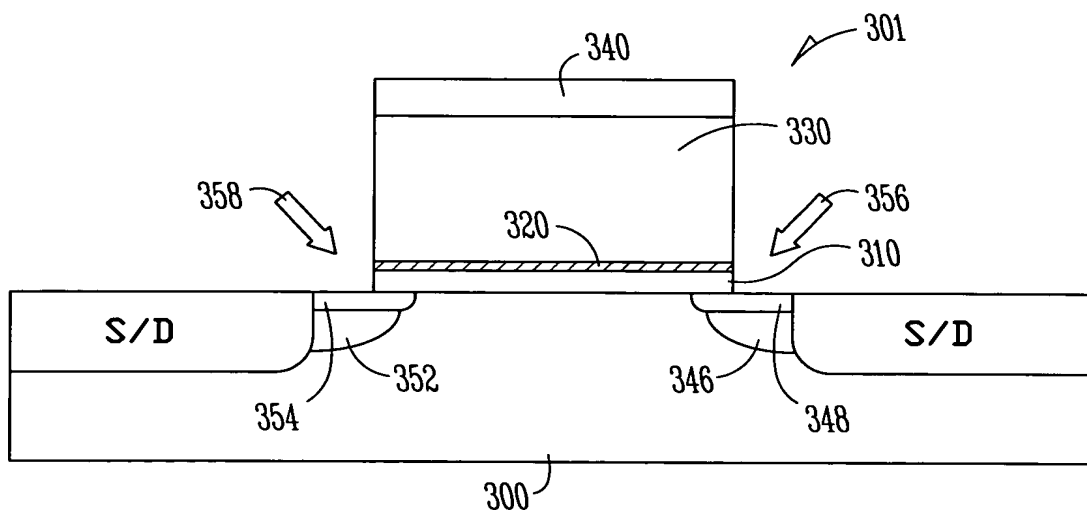
*Fig. 2b (Prior Art)*



*Fig. 2c (Prior Art)*



*Fig. 3a*

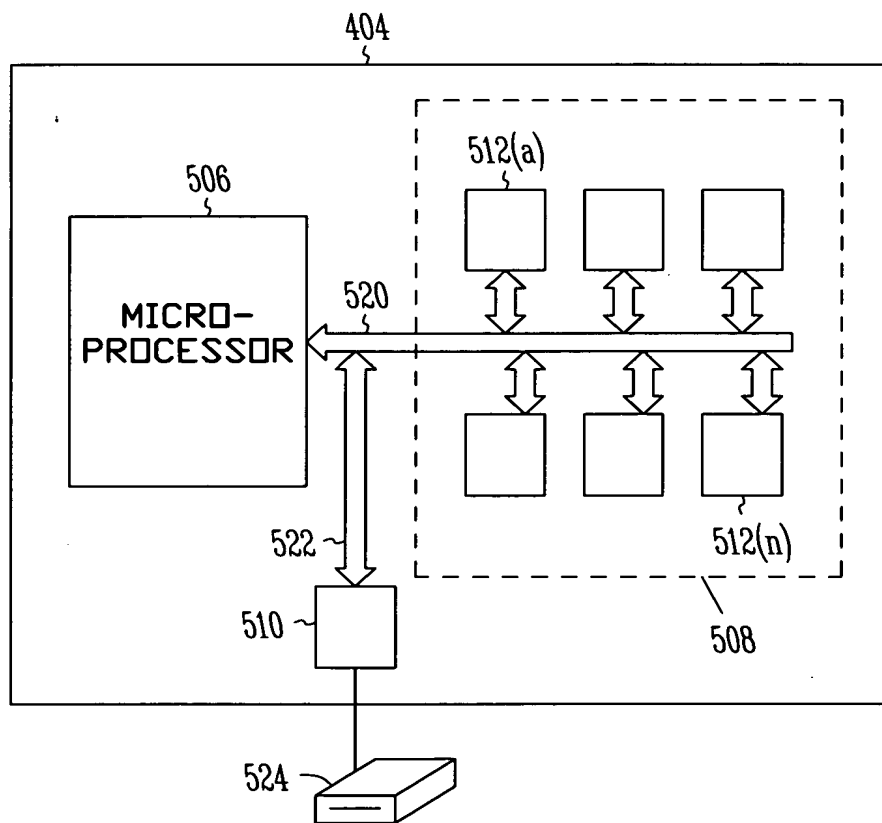
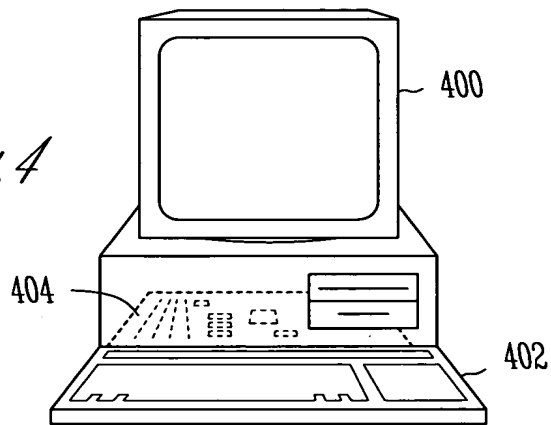


*Fig. 3b*

Fig. 3 is a cross-sectional view of a semiconductor device. It shows a central channel region 320 flanked by gate stack regions 310. The gate stack regions 310 are further flanked by source/drain regions 342, 346, and 348. The source/drain regions 342 and 346 are labeled "S/D". The gate stack regions 310 are labeled "3d-3d". The channel region 320 is labeled "300". The gate stack regions 310 are labeled "301". The source/drain regions 342 and 346 are labeled "360". The source/drain regions 346 and 348 are labeled "362". The source/drain regions 346 and 348 are labeled "364". The source/drain regions 346 and 348 are labeled "366". The source/drain regions 346 and 348 are labeled "368". The source/drain regions 346 and 348 are labeled "370".

*Fig. 3d*

*Fig. 4*



*Fig. 5*

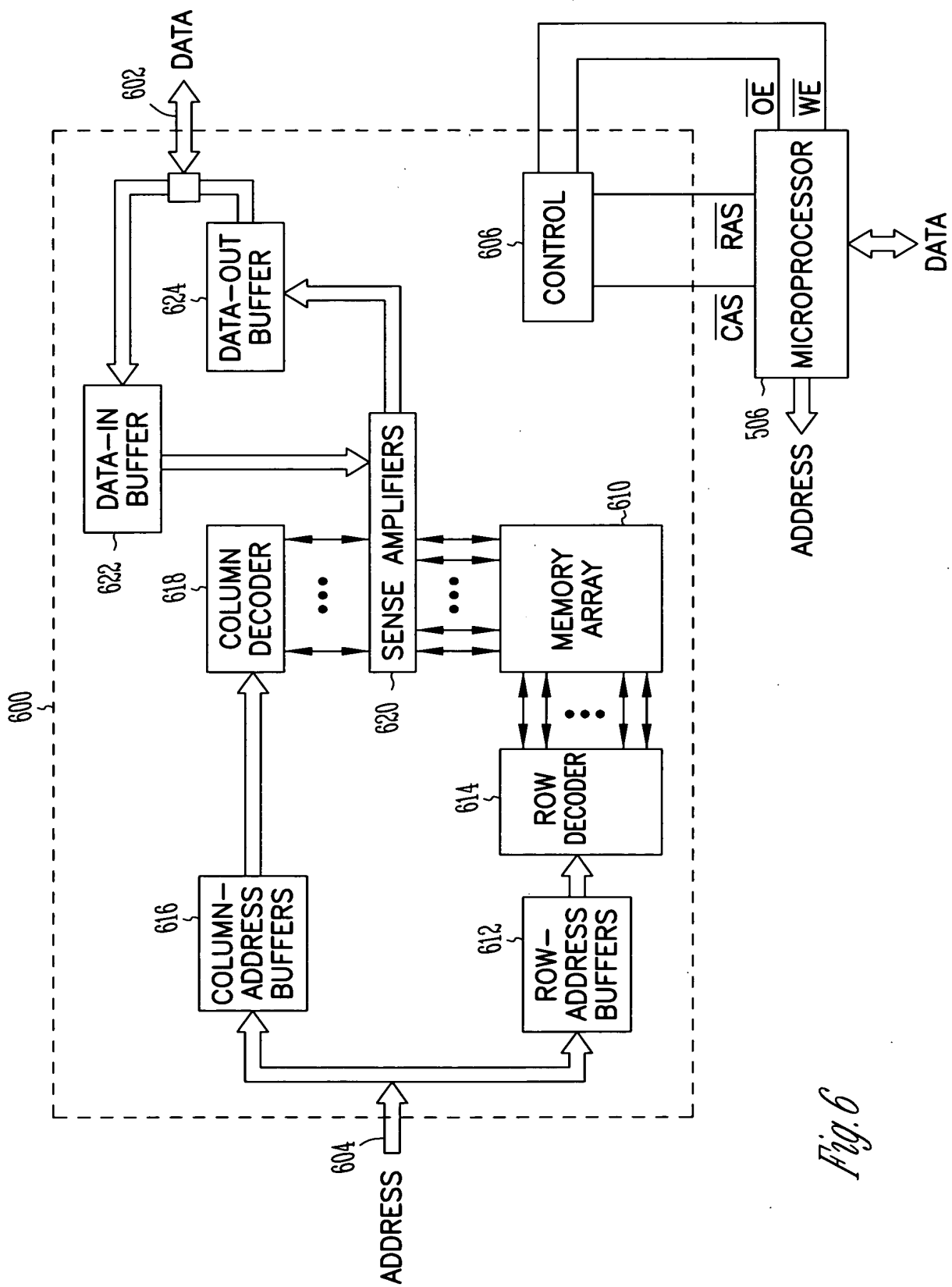


Fig. 6